**Diode Module** 

FRED

# **STARPOWER**

SEMICONDUCTOR™

# FD300HFS120C2S

**Molding Type Module** 

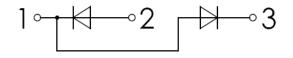
1200V/300A 2 in one-package

### **General Description**

STARPOWER Diode Power Module provides low forward voltage as well as low reverse recovery loss.They are designed for the applications such as SMPS.

### Features

- Fast soft diode
- Low forward voltage drop
- Small temperature coefficient
- Low reverse recovery losses
- High ruggedness
- Low inductance
- Isolated copper baseplate using DBC echnology



Equivalent Circuit Schematic

## **Typical Applications**

- SMPS
- PFC
- Electric welders
- DC choppers

Symbol	Description	FD300HFS120C2S	Units
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V
I <sub>F</sub>	Continuous Forward Current @ T <sub>C</sub> =80°C	300	А
I <sub>F RM</sub>	Repetitive Peak Forward Current	600	А
I <sub>FSM</sub>	Surge Forward Current $T_j=45^{\circ}C, V_R=0V$	3000	А
T <sub>j</sub>	Maximum Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-40 to +125	°C
I <sup>2</sup> t-value,Diode	V <sub>R</sub> =0V,t=10ms,T <sub>j</sub> =125 °C	19000	$A^2s$
V <sub>ISO</sub>	Isolation Voltage RMS,f=50Hz,t=1min	2500	V
Mounting Tongue	Power Terminal Screw:M5	2.5 to 5.0	N.m
Mounting Torque	Mounting Screw:M6	3.0 to 5.0	N.m

## Absolute Maximum Ratings $T_C=25$ °C unless otherwise noted

#### Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

### **Characteristics Values**

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
V <sub>F</sub>	Diode Forward		Tj=25℃		1.95	2.20	v
	Voltage	$I_{F}=300A, V_{GE}=0V$	Tj=125℃		1.85		
I <sub>R</sub>	Diode Reverse	V –V	T <sub>j</sub> =125°C			3.0	mA
	Current	V <sub>R</sub> =V <sub>RRM</sub>				5.0	
Qr	Recovered Charge	I <sub>F</sub> =300A,	T <sub>j</sub> =25℃		17.2		nC
			Tj=125℃		36.0		
I <sub>RM</sub>	Peak Reverse		Tj=25℃		120		A
	Recovery Current	$V_{R}$ =600V, di/dt=-3300A/µs,	T <sub>j</sub> =125℃		180		
E <sub>rec</sub>	Reverse Recovery	ui/ut=-3300A/μs,	Tj=25℃		5.8		mJ
	Energy		T <sub>j</sub> =125℃		13.2		
L <sub>CE</sub>	Stray Inductance					20	nH
R <sub>CC'+EE'</sub>	Module Lead						
	Resistance, $T_C=25^{\circ}C$				0.35		$m\Omega$
	Terminal To Chip	erminal To Chip					

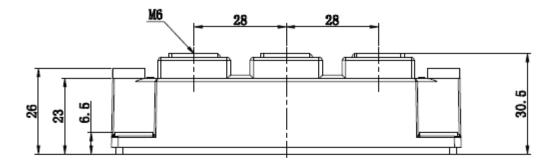
# **Thermal Characteristics**

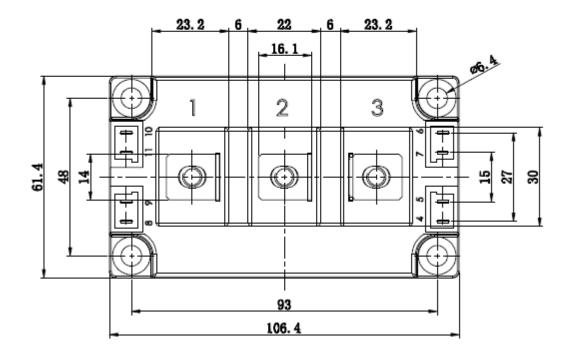
Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (DIODE Part,per 1/2 Module)		0.11	K/W
$R_{\theta CS}$	Case-to-Sink (conductive grease applied,per Module)	0.038		K/W
Weight	Weight of Module	300		g

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# **Package Dimension**

**Dimensions in Millimeters** 





### **Terms and Conditions of Usage**

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